



MODEL ANSWER
SUMMER– 18 EXAMINATION

Subject Title:- Electronic Engineering Materials

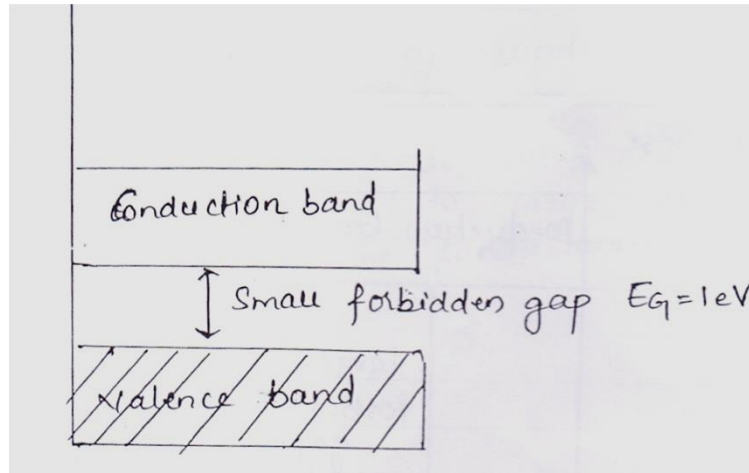
Subject Code:-

22217

Important Instructions to examiners:

- 1) The answers should be examined by key words and not as word-to-word as given in the model answer scheme.
- 2) The model answer and the answer written by candidate may vary but the examiner may try to assess the understanding level of the candidate.
- 3) The language errors such as grammatical, spelling errors should not be given more Importance (Not applicable for subject English and Communication Skills).
- 4) While assessing figures, examiner may give credit for principal components indicated in the figure. The figures drawn by candidate and model answer may vary. The examiner may give credit for any equivalent figure drawn.
- 5) Credits may be given step wise for numerical problems. In some cases, the assumed constant values may vary and there may be some difference in the candidate's answers and model answer.
- 6) In case of some questions credit may be given by judgement on part of examiner of relevant answer based on candidate's understanding.
- 7) For programming language papers, credit may be given to any other program based on equivalent concept.

Q. No.	Sub Q.N.	Answer	Marking Scheme
Q.1		Attempt any FIVE of the following :	10 Marks
	a)	Define the term 'Photoelectric emission.	2 Marks
	Ans:	Photoelectric emission is defined as "emission of electron from the metal surface, when illuminated by light"	2 Marks
	b)	List dielectric materials (any four).	2 Marks
	Ans:	i)Mica ii) Porcelain iii)polythene iv)Bakelite v)polyvinyl chloride vi)rubber vii)cotton viii)silk ix)glass x)paper &boards xi)wood xii) enamel covering xiii)transformer oil xiv)polymers.	Any four 1/2 Marks each
	c)	Define the term 'Permeability'. State its unit.	2 Marks
	Ans:	The capability of the magnetic material to conduct the magnetic flux is known as permeability. Unit :H/m or H m ⁻¹ (henries per meter),or N.A-2 (Newton per Ampere square)	1 Marks 1 Marks
	d)	Sketch energy band diagram of intrinsic semiconductor.	2 Marks
	Ans:		2 Marks



e)	List electrical conducting material (any four).		2 Marks
Ans:	Copper, gold ,silver ,aluminum , mercury ,steel, iron, sea water		1/2 marks each
f)	‘Pentavalent impurity materials are called as Donor impurity.’ Justify your answer.		2 Marks
Ans:	Pentavalent impurity materials like Arsenic ,phosphorus and Antimony has 5 valence electron ,out of which four are utilized in bonding with intrinsic semiconductor like silicon or germanium and the one electron left is donated to act as charge carrier hence, Pentavalent impurity materials are called as Donor impurity.’		2 Marks
g)	State working principle of LED.		2 Marks
Ans:	LED works on the principle of “electroluminescence” In electroluminescent materials, which are semiconductors the energy of an electric filed produces a localized high free charge carrier density and light is emitted when the free charge carrier combine.		1 Marks 1 Marks
Q 2	Attempt any THREE :		12 Marks
a)	State the effect of following factors on resistivity of electrical conducting material :(i) Temperature (ii) Alloying (iii) Cold work (iv) Age Hardening		4 Marks
Ans:	(i)Temperature: As the temperature increases the resistivity of material increases, hence conductivity decreases. (ii) Alloying: Addition of another metal to a pure metal will increase the resistivity considerably hence conductivity decreases. (iii) Cold work: Mechanical distortion taking place in metal increases resistivity of a metal thereby decreasing the conductivity.		1 Marks 1 Marks 1 Marks



	<p>(iv) Age Hardening: The age hardness of conducting material increases the resistivity which decreases the conductivity.</p>	
b)	State four selection factors for selecting an insulating material.	4 Marks
Ans:	<p>Four selection factors for selecting an insulating material are</p> <p>i)Electrical ii)Mechanical iii)Thermal iv)Chemical</p> <p>i) Electrical factor: A good insulating material should have high resistivity and low leakage current. It should have high dielectric strength and small dielectric loss.</p> <p>ii) Mechanical factor: A good insulating material should have sufficient mechanical strength to withstand vibrations.</p> <p>iii) Thermal factor: A good insulating material should have small thermal expansion to avoid damages, It should be non ignitable and self extinguishable.</p> <p>iv) Chemical factor: A good insulating material should be resistant to oils, gas, fumes acids and alkalis. It should not absorb water as water reduces insulation resistance and dielectric strength.</p>	<p>1 Marks</p> <p>1 Marks</p> <p>1 Marks</p> <p>1 Marks</p>
c)	Describe the effect on the capacitance of the dielectric material on the basis of factors polarizability and permittivity.	4 Marks
Ans:	<p>The function of a capacitor is to store charge. its capacity to store charge is measured in terms of capacitance (C)</p> <p>The presence of dielectric material between the two conducting material in capacitor helps the capacitor to store charge or else the circuit gets completed and current starts flowing.</p> <p>When electric field is applied across the dielectric material ,the electrons of atoms are acted upon by the electric field and are displaced in a direction opposite to that of electric field this results in seperation of positive and negative charges hence dipoles are created in the dielectric material and said to be polarized</p>	2 Marks



The capacitance of a capacitor in vacuum is given as $C_0 = \frac{Q_0}{A}$

The capacitance of a capacitor in solid dielectric is given as $C = \frac{Q}{A}$

But $C \propto \frac{A}{d}$

where, A = Area of cross section of metal plates
 d = distance between metal plates.

∴ for solid dielectric $C = \frac{E A}{d}$

for vacuum dielectric $C_0 = \frac{E_0 A}{d}$

where E = Absolute permittivity of solid dielectric
 E_0 = Absolute permittivity of vacuum dielectric

∴ $\frac{C}{C_0} = \frac{E}{E_0}$

$\frac{C}{C_0} = E_r$ (Relative permittivity or dielectric constant)

2 Marks

d) Describe Peltier thermoelectric effect. State its application.

4 Marks

Ans: 1. Thermoelectric effect deals with relation between heat and electrical energy. The motion of electron gets altered by the flow of current or temperature gradient. This is the basis of thermoelectric effect.

3 Marks

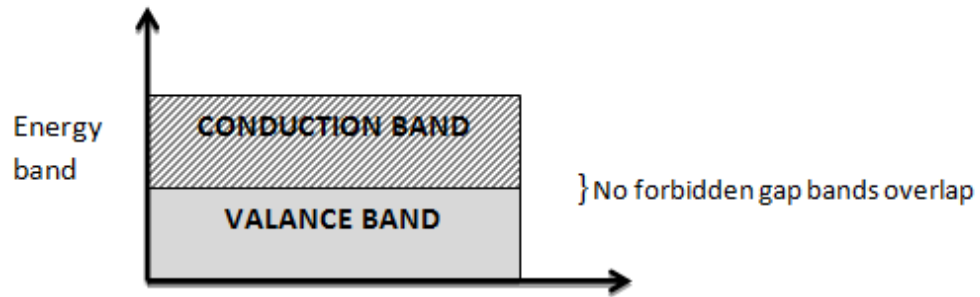


	<p>2. When a current is passed through the junction of two different metals then heat is absorbed or liberated depending on the direction of current this effect is called as Peltier effect.</p> <p>3. The heat is called as Peltier heat. Peltier heat is reversible which means that the absorption can be changed to liberation by reversing the direction of current.</p> <p>Application: This effect is used in Refrigeration</p>	1 Marks															
Q. 3	Attempt any THREE :	12 Marks															
a)	<p>Compare P-type semiconductor with N-type semiconductor on the basis of</p> <p>(i) Majority charge carrier (ii) Minority charge carrier (iii) Impurity material (iv) Fermi-level position in energy band diagram.</p>	4 Marks															
Ans:	<table border="1"> <thead> <tr> <th></th> <th>P-type semiconductor</th> <th>N-type semiconductor</th> </tr> </thead> <tbody> <tr> <td>(i) Majority charge carrier</td> <td>Holes</td> <td>Electron</td> </tr> <tr> <td>(ii) Minority charge carrier</td> <td>Electron</td> <td>Holes</td> </tr> <tr> <td>(iii) Impurity material</td> <td>Trivalent such as Boron, calcium Indium etc</td> <td>Pentavalent such as Phosphorous antimony arsenic</td> </tr> <tr> <td>(iv) Fermi-level position in energy band diagram.</td> <td>Fermi level lies towards valance band</td> <td>Fermi levels lies towards conduction band</td> </tr> </tbody> </table>		P-type semiconductor	N-type semiconductor	(i) Majority charge carrier	Holes	Electron	(ii) Minority charge carrier	Electron	Holes	(iii) Impurity material	Trivalent such as Boron, calcium Indium etc	Pentavalent such as Phosphorous antimony arsenic	(iv) Fermi-level position in energy band diagram.	Fermi level lies towards valance band	Fermi levels lies towards conduction band	1 marks for each point
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b)	List specifications of micro relay. (any four)	4 Marks															
Ans:	<p>specifications of micro relay are :</p> <p>1) Contact arrangement 2) Limiting making current 3) Limiting breaking current 4) Overload current</p>	1 marks for each point															
c)	Sketch energy band diagram of conducting and insulating material and label it well.	4 Marks															
Ans:																	

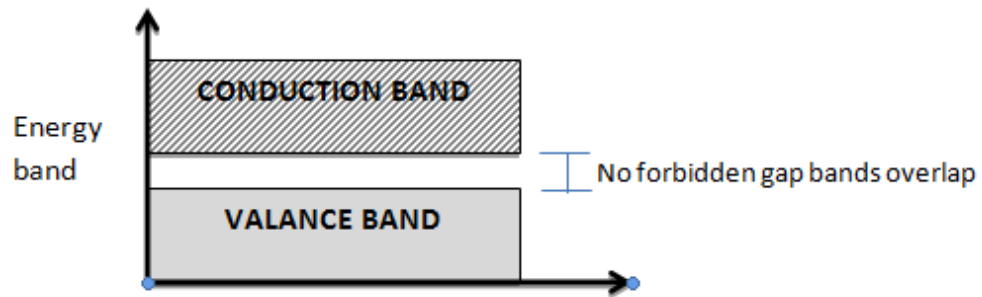


2 Marks
for each
diagram

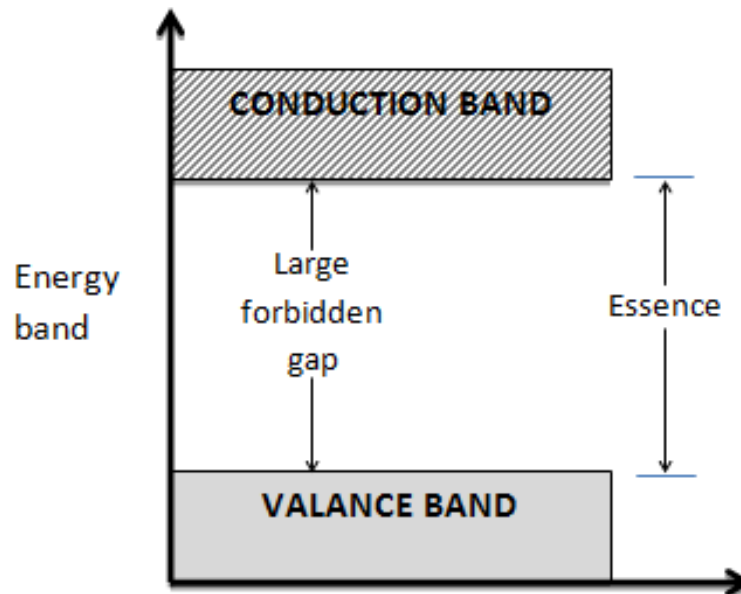
(i) Energy band diagram of conducting material



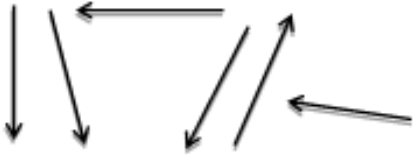
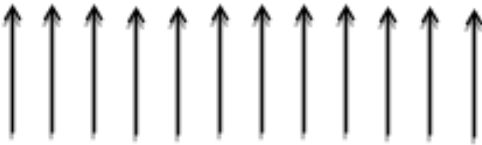
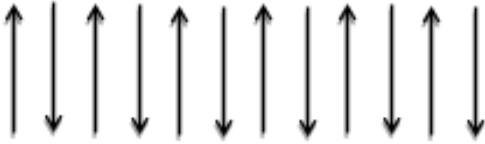
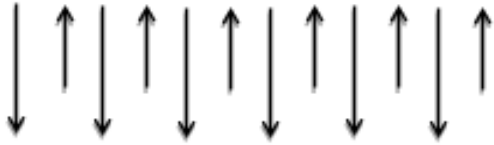
OR



(ii) Energy band diagram of insulating material





d)	Sketch orientation of spins in paramagnetic, ferromagnetic, anti-ferromagnetic and ferrimagnetic material.	4 Marks
Ans:	<p>(i) Paramagnetic</p>  <p>Spins are randomly oriented</p> <p>(ii) Ferromagnetic</p>  <p>Spins are aligned parallel in magnetic domains</p> <p>(iii) Anti-Ferromagnetic</p>  <p>Spins are aligned antiparallel in magnetic domains</p> <p>(iv) Ferrimagnetic</p>  <p>Spins are aligned antiparallel but do not cancel</p>	1 Marks for each diagram
Q. 4	Attempt any THREE :	12 Marks
a)	State any two characteristics of (i) Electro-textile (ii) Textile-antenna used for wearable antenna.	4 Marks
Ans:	Characteristics of :- i. Electro-textile 1) They have excellent radio frequency performance	Any two characteristics-

	<p>2) They get more and more attention for body centric communication 3) They adopt woven pattern</p> <p>ii. Textile-antenna</p> <p>1) The bandwidth of these antennas is between 2.52 GHz to 13.35 GHz 2) Textile materials get easily integrated into clothes and other wearable devices 3) It has very low dielectric constant that reduces the surface wave losses. 4) Increases the impedance bandwidth for the antenna.</p>	<p>1 Mark each</p> <p>Any two characteristics- 1 Mark each</p>
b)	Describe the concept of ferroelectricity. State its applications.	4 Marks
Ans:	<p><u>Concept of Ferro electricity:-</u></p> <p>Ferro electricity is the property of certain materials, that exhibit spontaneous electric polarization i.e. separation of positive and negative electric charge. Making one side of the positive and opposite side negative that can be reversed in direction by the application of an electric field. It contains small region which are polarized in different electronics filed. The Ferro electricity bears a close analogy to ferromagnetism.</p> <p><u>Application:-</u></p> <p>It is used in condensers to concentrate considerable quantities of electric energy within a small space.</p>	<p>2 Marks for concept</p> <p>2 Marks for application</p>
c)	Describe with sketch B-H curve. State effect of change in temperature on area of B—H curve.	4 Marks
Ans:	<p>The diagram shows a hysteresis loop on a B-H coordinate system. The vertical axis is labeled B and the horizontal axis is labeled H. The origin is O. The loop is a closed curve with arrows indicating the direction of magnetization. Key points on the loop are labeled P (top right), Q (top left), R (left), S (bottom left), T (bottom), and U (bottom right). A dashed line from P to the B-axis is labeled B_m. A dashed line from P to the H-axis is labeled H_m. A dashed line from U to the H-axis is labeled H_c. The area under the curve is labeled Ag(a). The signature 'OY' is written at the bottom right of the diagram.</p> <p style="text-align: center;">OR</p>	2 Marks for diagram

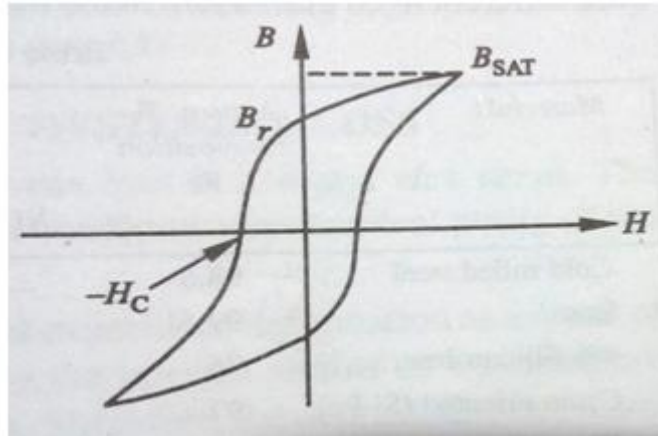


Fig (b)

The B-H curve can be plotted by increasing and decreasing the field intensity. It is shown in fig (b)

Below the Curie temperature all ferromagnetic materials exhibit the well known hysteresis in the B versus H curve. Starting with an unmagnetized specimen, B varies reversibly with H for small fields. Since there is no hysteresis in this region, one defines the initial permeability, μ_r , in the same way as the permeability of a paramagnetic material. As the field H is increased, B begins to increase rapidly and ultimately approaches a saturation value B_{sat} . Upon reducing the value of H from the saturation region to zero, it is observed that there remains a flux density B_r , called the remnant flux density. Since $H = 0$, the material must be permanently magnetized; in fact, the magnetization corresponding to B_r is equal to B_r / μ_0 . The field $-H_c$ required to reduce the flux density to zero is called the coercive force.

Effect of change in temperature on area of B-H curve

It is shown that at Curie temperature saturation magnetization becomes zero and above that it becomes paramagnetic materials exhibit the well known phenomenon of hysteresis in the magnetization.

**1 Marks
for
description**

**1 Marks
for effect**

d) State effect of temperature on superconductivity of metals. 4 Marks

Ans: In the superconducting state, a material possesses zero electrical resistance and behaves as a perfectly diamagnetic material, above critical temperature T_c , superconducting property of the material is destroyed and material reverts back to its normal state. **4 Marks**

e) State any two properties and application of following material : 4 Marks

- (i) Mica
- (ii) Transformer oil
- (iii) Rubber
- (iv) Polymer

Ans:



		<p>(i) Mica</p> <p><u>Properties</u></p> <ol style="list-style-type: none">1. It is excellent insulation properties2. It release water when heated3. It has inorganic mineral material <p><u>Applications</u></p> <ol style="list-style-type: none">1. It is used in radio circuits, capacitor, radio tubes, segment insulation etc.2. It is used in high voltage machines, traction motors, switches, plugs, fuse, holder, parts of sockets etc. <p>(ii) Transformer oil</p> <p><u>Properties</u></p> <ol style="list-style-type: none">1. It has higher resistivity2. It has small viscosity3. It has low density <p><u>Applications</u></p> <ol style="list-style-type: none">1. It is used for impregnation2. It is used high voltage transformers, capacitors. <p>(iii) Rubber</p> <p><u>Properties</u></p> <ol style="list-style-type: none">1. It is an elastic substance2. The vulcanized rubber is stretchable and elastic3. <p><u>Application</u></p> <ol style="list-style-type: none">1. It is used in flexible wires, jack cards and installation wires2. It is used in manufacturing tubes, tyres etc. <p>(iv) Polymer</p> <p><u>Properties</u></p> <ol style="list-style-type: none">1. It can be molded2. It has ability to soften and even melt <p><u>Application</u></p> <ol style="list-style-type: none">1. It is used to produce yarns, cloths and films2. The synthetic resins are popular in the electrical installations.	<p>1 Marks for any two properties</p> <p>1 Marks for any two applications</p>
Q.5		Attempt any TWO :	12 Marks
	a)	The resistivity of pure copper is $1.56 \mu\Omega\text{-cm}$. An alloy of copper containing 1 atomic percent nickel has a resistivity of $2.81 \mu\Omega\text{-cm}$. An alloy of copper containing 3 atomic percent silver has a resistivity of $1.98 \mu\Omega\text{-cm}$. Calculate the resistivity of copper alloy containing 2 atomic percent nickel and 2 atomic percent silver.	6 Marks



Ans:

Solution:- Resistivity of pure copper (ρ_{Cu})
 $\rho_{Cu} = 1.56 \mu\Omega\text{cm}$ (given)

Resistivity of alloy of copper and 1 atomic percent
Nickel = $2.81 \mu\Omega\text{cm}$ (given)

$$\text{ie } \rho_{(Cu+Ni)} = 2.81 \mu\Omega\text{cm}$$

$$\therefore \rho_{Ni} = \rho_{(Cu+Ni)} - \rho_{Cu} \quad (2M)$$

$$\therefore \rho_{Ni} = 2.81 - 1.56$$

$$\boxed{\rho_{Ni} = 1.25 \mu\Omega\text{cm}}$$

Alloy of copper containing 3 atomic percent silver has
resistivity of $1.98 \mu\Omega\text{cm}$

$$\text{ie } \rho_{Cu} + 3 \times \rho_{Ag} = 1.98$$

$$1.56 + 3 \times \rho_{Ag} = 1.98 \quad (2M)$$

$$\rho_{Ag} = \frac{1.98 - 1.56}{3}$$

$$\boxed{\rho_{Ag} = 0.14 \mu\Omega\text{cm}}$$

To calculate resistivity of copper alloy
containing 2 atomic percent Nickel and 2 atomic
percent Silver

$$\rho_{(Cu+Ni+Ag)} = \rho_{Cu} + 2 \times \rho_{Ni} + 2 \times \rho_{Ag} \quad (2M)$$

$$= 1.56 + 2 \times 1.25 + 2 \times 0.14$$

$$= 1.56 + 2.5 + 0.28$$

$$\boxed{\rho_{(Cu+Ni+Ag)} = 4.34 \mu\Omega\text{cm}}$$

2 Marks

2 Marks

2 Marks

b)

Classify following material as diamagnetic, paramagnetic, ferromagnetic and anti-ferromagnetic :

(i) Platinum

(ii) Iron

(iii) Glass

(iv) Nickel oxide

(v) Quartz

6 Marks



		(vi) Silicon Iron alloy															
	Ans:	<table border="1"> <thead> <tr> <th>Materials</th> <th>Classification</th> </tr> </thead> <tbody> <tr> <td>(i) Platinum</td> <td>Paramagnetic</td> </tr> <tr> <td>(ii) Iron</td> <td>Ferromagnetic</td> </tr> <tr> <td>(iii) Glass</td> <td>Diamagnetic</td> </tr> <tr> <td>(iv) Nickel oxide</td> <td>Anti -ferromagnetic</td> </tr> <tr> <td>(V) Quartz</td> <td>Diamagnetic</td> </tr> <tr> <td>(vi) Silicon Iron alloy</td> <td>Ferromagnetic</td> </tr> </tbody> </table>	Materials	Classification	(i) Platinum	Paramagnetic	(ii) Iron	Ferromagnetic	(iii) Glass	Diamagnetic	(iv) Nickel oxide	Anti -ferromagnetic	(V) Quartz	Diamagnetic	(vi) Silicon Iron alloy	Ferromagnetic	1 Marks each
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	c)	Describe effect of plate area, thickness of dielectric material, permittivity on capacitance of a capacitor.	6 Marks														
	Ans:	<p>The capacitance of capacitor in vacuum is given as</p> $C_0 = \frac{Q_0}{V}$ <p>The capacitance of a capacitor in solid dielectric is given as</p> $C = \frac{Q}{V}$ <p>The capacitance of a parallel plate capacitor is given as</p> $C = \frac{\epsilon A}{d}$ <p>Where</p> <ol style="list-style-type: none"> 1. "A" is the cross sectional area of metal plates and it is directly proportional to capacitance. As "A" increases Capacitance is also increases. 2. "d" is the thickness of dielectric material and it is inversely proportional to capacitance. As "d" increases Capacitance is also decreases and vice-versa. 3. "ε" is the relative permittivity of free space and it is directly proportional to capacitance. As "ε" increases "C" also increases. 	<p>1 Marks</p> <p>2 Marks</p> <p>1 Marks</p> <p>1 Marks</p> <p>1 Marks</p>														
Q.6	A)	Attempt any TWO :	12 Marks														
	a)	Explain thermal conductivity and coefficient of thermal conductivity in semiconductor material.	6 Marks														
	Ans:	<p>Thermal conductivity:-</p> <p>Thermal conductivity (often denoted k, λ, or κ) is the property of a material to conduct heat. It is evaluated primarily in terms of the Fourier's Law for heat conduction. In general, thermal conductivity is a tensor property, expressing the anisotropy of the property.</p> <p>Heat transfer occurs at a lower rate in materials of low thermal conductivity than in materials of high thermal conductivity. Correspondingly, materials of high thermal conductivity are widely used in heat sink applications and materials of low thermal conductivity are used as thermal insulation. The thermal conductivity of a material may depend on temperature.</p> <p>Examples of Coefficient of thermal conductivity in semiconductor material:-</p>	3 Marks														



		<table border="1"><thead><tr><th>Semiconductors</th><th>Thermal Conductivity (k)</th></tr></thead><tbody><tr><td>AlGaAs</td><td>90</td></tr><tr><td>GaAs</td><td>46 to 55</td></tr><tr><td>GaN</td><td>40 to 130</td></tr><tr><td>Ge</td><td>58 to 60</td></tr><tr><td>InP</td><td>68</td></tr><tr><td>Si</td><td>140 to 163</td></tr><tr><td>SiC</td><td>16 to 55</td></tr></tbody></table>	Semiconductors	Thermal Conductivity (k)	AlGaAs	90	GaAs	46 to 55	GaN	40 to 130	Ge	58 to 60	InP	68	Si	140 to 163	SiC	16 to 55	3 Marks
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b)	Explain hysteresis loss and eddy current loss of magnetic material.		6 Marks																
Ans:	<p>Hysteresis loss of magnetic material:-</p> <ul style="list-style-type: none">• It is also known as Iron Loss or Core Loss and it is always constant.• Hysteresis loss is due to the reversal of magnetization of transformer core whenever it is subjected to alternating nature of magnetizing force .Whenever the core is subjected to an alternating magnetic field, the domain present in the material will change their orientation after every half cycle. The power consumed by the magnetic domains for changing the orientation after every half cycle is called Hysteresis loss.• <p>Eddy current loss of magnetic material:-</p> <ul style="list-style-type: none">• When an alternating magnetic field is applied to a magnetic material an emf is induced in the material itself according to Faraday's Law of Electromagnetic induction. Since the magnetic material is a conducting material, these EMFs circulates currents within the body of the material. These circulating currents are called Eddy Currents. Eddy current will occur when the conductor experiences a changing magnetic field. It produces a loss (I^2R loss) in the magnetic material known as an Eddy Current Loss.• Similar to hysteresis loss, eddy current loss also increases the temperature of the magnetic material. The hysteresis and the eddy current losses in a magnetic material are also known by the name iron losses or core losses or magnetic losses.	3 Marks 3 Marks																	

		<p>Diagram is optional.</p>
<p>c)</p>	<p>Suggest two passive materials used for substrate. metal and capacitance of semiconductor device fabrication. State their two functions.</p>	<p>6 Marks</p>
<p>Ans:</p>	<p>Passive materials</p> <p>(i) Substrate: most widely used substrate are either plastic, glass or ceramic. Functions:</p> <ul style="list-style-type: none"> i) They are used for deposition of thin films layers. (ii) Plastic substrate is used only for thin film solar cells. (iv) Glass or ceramic are used for deposition of metals for resistors and capacitors <p>(ii) Metals: Commonly used metals are gold, platinum, Aluminium, Nickel-chromium . Functions :</p> <ul style="list-style-type: none"> (i) They act as capacitor plates (ii) They are used for resistors (iii) For mechanical support. (iv) As heat dissipater. <p>(iii) Capacitance materials : commonly used capacitance material are SiO, ZnS, SiO₂, TiO₂, BaTiO₂, MgF₂, Ta₂O₅, Al₂O₃ Functions :</p> <ul style="list-style-type: none"> (i) a pin-hole free continuous layer (ii) High dielectric constant (iii) A low loss factor at the desired frequency (iv) Ability to withstand thermal stresses without cracking 	<p>1 Marks (Any 2)</p> <p>1 Marks (Any 2)</p> <p>1 Marks (Any 2)</p> <p>1 Marks (Any 2)</p> <p>1 Marks (Any 2)</p>